MOTOROLA SEMICONDUCTOR I **TECHNICAL DATA**

The RF Line **UHF Power Amplifier**

 \dots designed for 13 Volt UHF power amplifier applications in industrial and commercial FM equipment operating from 890 to 915 MHz.

• Specified 13 Volt, UHF Characteristics

Output Power = 12 Watts

Minimum Gain = 20.8 dB

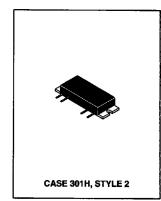
Harmonics = -42 dBc Max (2f₀)

-60 dBc Max (3fo and Higher)

- 50 Ω Input/Output Impedances
- Guaranteed Stability and Ruggedness
- · Features Three Common-Emitter Gain Stages
- Epoxy Glass PCB Construction Gives Consistent Performance and Reliability
- Gold-Metallized and Silicon Nitride-Passivated Transistor Chips
- Controllable, Stable Performance Over More Than 35 dB Range in Output Power

MHW812A3

12 W, 890-915 MHz HIGH GAIN RF POWER **AMPLIFIERS**



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Supply Voltages	V _{s1}	16	Vdc
RF Input Power	Pin	200	mW
RF Output Power	Pout	15	w
Storage Temperature Range	T _{stg}	-30 to +100	-€
Operating Case Temperature Range	TC	-30 to +100	-€
DC Control Voltage	VCont	12.5	Vdc

ELECTRICAL CHARACTERISTICS (Flange Temperature = 25° C, 50 Ω system, and V_{S1} = 13 V unless otherwise noted)

Charac	teristic	Symbol	Min	Тур	Max	Unit
Frequency Range		BW	890	_	915	MHz
Power Gain (VCont = 12.5 Vdc, Pout = 12 W)	Gp	20.8	21.5	-	dB
Efficiency (1) (Pout = 12 W)		η	40	45	_	%
Harmonic Output (1) (P _{OUt} = 12 W Reference)	2f ₀ 3f ₀ and Higher	_	_	_	-42 -60	dBc
Input VSWR (1) $(P_{Out} = 12 \text{ W}, 50 \Omega \text{ Reference, F}$ Eliminate Harmonic Content)	leflected Signal Filtered to	VSWRin	_	_	2:1	_

NOTE:

1. Pin = 100 mW; adjust VCont for specified Pout-

(continued)

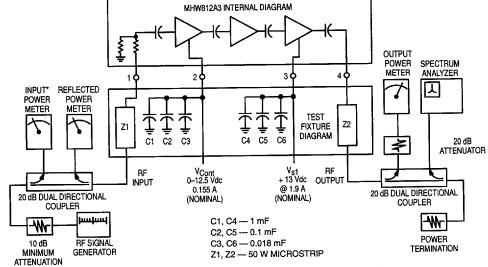
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Characte	eristic	Symbol	Min	Тур	Max	Unit	
Power Degradation (-30 to +80°C) (1) (Reference Pout = 12 W @ T _C = 25°C)		_			1.7	dB	
oad Mismatch Stress (1) (V _S 1 = 16 Vdc, P _{Out} = 13 W, VSWR = 30:1, all phase angles)		Ψ	No degradation in Power Output				
Stability (P _{in} = 0 to 200 mW, V _{S1} = 10 to 16 Vdc, V _{Cont} = 0 to 12.5 Vdc, Load VSWR = 4:1, P _{OUT} Max = 13 W) (2)			All spurious outputs ≽ 70 dB below desired output signal level				
Quiescent Current @ V _{Cont} = 12.5 V (I _{Cont} with no RF drive applied)		lCont	_	_	225	mA	
Control Voltage	Pin = 100 mW	VCont	0	9	12.5	Vdc	
Control Current	P _{out} = 12 W V Cont = 12.5 V	l _{Cont}	0	155	225	mA	

NOTES:

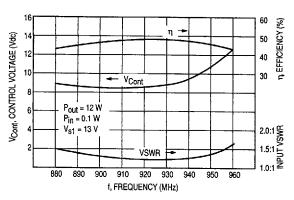
- 1. P_{in} = 100 mW; adjust V_{Cont} for specified P_{out}. 2. Combination of P_{in}, V_{s1} and V_{Cont} can not exceed max P_{out} = 15 W.



*Module input power is forward power as sampled by the directional coupler and read on the input power meter.

Figure 1. UHF Power Amplifier Test System Diagram

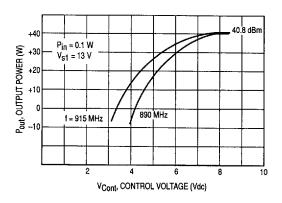
TYPICAL CHARACTERISTICS



f = 890 MHz P_{out}, OUTPUT POWER (W) 8 0 17 17 15 8 6 950 MHz V_S = 13 V V_{Cont} = 12.5 V 25 75 0 50 100 125 150 175 200 P_{ID}, INPUT POWER (mW)

Figure 2. Control Voltage, Efficiency and VSWR versus Frequency

Figure 3. Output Power versus Input Power



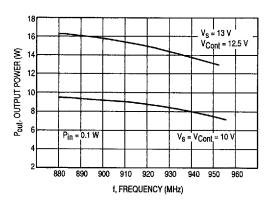
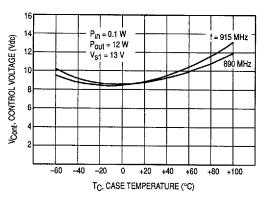


Figure 4. Output Power versus Control Voltage

Figure 5. Output Power versus Frequency



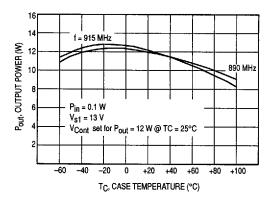


Figure 6. Control Voltage versus Case Temperature

Figure 7. Output Power versus Case Temperature

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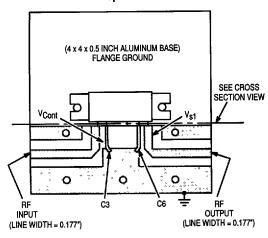
Nominal Operation

All electrical specifications are based on the following nominal conditions: ($P_{out} = 12 \text{ W}, V_{s1} = 13 \text{ Vdc}$). This module is designed to have excess gain margin with ruggedness, but operation outside the limits of the published specifications is not recommended unless prior communications regarding the intended use have been made with a factory representative.

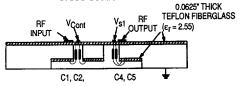
Gain Control

In general, the module output power should be limited to 13 watts. The preferred method of power output control is to fix V_{S1} at 13 volts, set RF drive level and vary the control voltage from 0 to 12.5 Volts. As designed, the module exhibits a gain control range greater than 35 dB using the method described above.

Top View



Cross Section View



Bring capacitor leads through fiberglass board and solder to V_{s1} and V_{Cont} lines as close to module as possible.

Figure 9. Test Fixture Construction

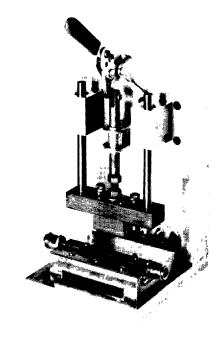


Figure 8. Test Fixture Assembly

Decoupling

Due to the high gain of each of the three stages and the module size limitation, external decoupling networks require careful consideration. Both Pins 2 and 3 are internally bypassed with a 0.018 µF chip capacitor which is effective for frequencies from 5 MHz through 960 MHz. For bypassing frequencies below 5 MHz, networks equivalent to that shown in the test fixture schematic are recommended. Inadequate decoupling will result in spurious outputs at specific operating frequencies and phase angles of input and output VSWR.

Load Mismatch Stress

During final test, each module is load mismatch stress tested in a fixture having the identical decoupling network described in Figure 1. Electrical conditions are V_{S1} equal to 16 volts, load VSWR 30:1 and output power equal to 13 watts.

Mounting Considerations

To insure optimum heat transfer from the flange to heatsink, use standard 6-32 mounting screws and an adequate quantity of silicone thermal compound (e.g., Dow Corning 340). With both mounting screws finger tight, alternately torque down the screws to 4-6 inch pounds. The heatsink mounting surface directly beneath the module flange should be flat to within 0.0015 inch. For more information on module mounting, see EB-107.